## InGaAs-APD/Preamp\_ Receiver

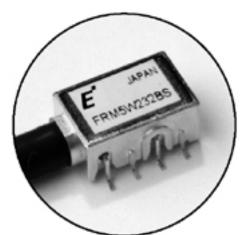
# FRM5W232BS/BS-A

### **FEATURES**

- 2.7Gb/s APD Receiver module in an industry standard mini-DIL package is available in gull-wing or through-hole configuration
- High Sensitivity: -34 dBm (typ.)
- Differential Electrical Output
- Integral Thermistor and GaAs IC Preamp
- Wide operating temperature range: -40 to +85°C



This APD detector preamp is intended to function as an optical receiver in long haul SONET, SDH, and DWDM systems operating up to 2.7Gb/s. The device operates in both the 1,310 and 1,550nm wavelength windows. The nominal 10KΩ integral thermistor allows accurate monitoring of the APD temperature and facilitates the design of the APD bias control circuits. The detector preamplifier has a differential electrical output.



### **DESCRIPTION**

The FRM5W232BS incorporates a 30 micron InGaAs Avalanche Photodiode (APD) detector, a GaAs IC transimpedance preamplifier, and a thermistor in a mini-DIL type package. The APD is processed with modern MOVPE techniques resulting in reliable performance over a wide range of operating conditions. The lens coupling system and the single mode fiber are assembled using Nd: YAG welding techniques. The BS package is designed for a surface mount PC board assembly, and the BS-A is designed for through-hole mount assembly.

### ABSOLUTE MAXIMUM RATINGS (T<sub>c</sub>=25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit	
Storage Temperature	T <sub>stg</sub>	-40 to +85	°C	
Operating Case Temperature	T <sub>op</sub>	-40 to +85	°C	
Supply Voltage	V <sub>DD</sub>	0 to +4.5	V	
APD Reverse Voltage	VR	0 to V <sub>B</sub> (Note)	V	
APD Reverse Current	IR(peak)	3.0	mA	

Note: Since the VB may vary from device to device, VB data is attached to each device for reference.



### **OPTICAL & ELECTRICAL CHARACTERISTICS**

(T<sub>C</sub>=25°C,  $\lambda$ =1,550nm, V<sub>DD</sub>=+3.3V unless otherwise specified)

Parameter	Symbol	Test Conditions		Min.	Limits Typ.	Max.	Unit	
APD Responsivity	R13	λ = 1,310nm, M=1		0.75	0.80	-		
	R15	λ =	: 1,550nm, M=1	0.80	0.85	-	A/W	
	R16	λ =	: 1,610nm, M=1	-	0.70	-		
APD Breakdown Voltage	VB	ID=10μA		40	50	65	V	
Temperature Coefficient of VB	γ	Note (1)		0.08	0.12	0.15	V/°C	
AC Transimpedance	Zt	Pin=-30dBm, f=100MHz, Single-end		1800	2200	2600	Ω	
Bandwidth	BW	Pin=-30dBm, M=10, -3dB from 1MHz		2.2	2.4	-	GHz	
Lower Cut-Off Frequency	fcl			-	50	75	kHz	
Peaking	dpk	Pin=-30dBm, M=10, from 1MHz		-	-	+2	dB	
Group Delay Deviation	GD	Pin=-30dBm, M=10, from 500MHz to 1.75GHz		-	100	-	psec	
Output Return Loss	S22	up to 1.75GHz		10	-	-	dB	
		up to 2.5GHz		5	-	-		
Equivalent Input Noise Current Density	in	Average within 2.2GHz		-	9.5	11	pA√Hz	
Minimum Sensitivity	Pr	Note (4)	Ta=25°C, Rext=14dB	-	-34.0	-33.0	dBm	
			Ta=-40°C ~ 85°C, Rext=14dB	-	-33.0	-31.0		
			Ta=25°C, Rext=10dB	-	-33.0	-		
Maximum Overload	P <sub>max</sub>	2.488Gb/s, NRZ, PRBS=2 <sup>23</sup> -1, BER=10 <sup>-10</sup> , M=3		-5	-	-	dBm	
		M=3, Note (3)		-7		-		
Maximum Output Voltage Swing	V <sub>clip</sub>	Saturated Output Voltage		450	550	800	mV	
Optical Return Loss	ORL	-		30	-	-	dB	
Power Supply Current	IDD	-		-	45	70	mA	
Power Supply Voltage	$V_{DD}$	-		3.15	3.30	3.45	V	
Thermistor Resistance	Rth	Tc=25°C		9.5	10.0	10.5	kΩ	
Thermistor B Constant	В	-		3800	3900	4000	К	

Note: (1)  $\gamma$ = $\Delta$ VB/ $\Delta$ Tc

Note: (2) All the parameters are measured with  $50\Omega$  AC-coupled.

Note: (3) Defined by 10% distortion of wave form.

Note: (4) Test condition is 2.488Gb/s, NRZ, PRBS=2<sup>23</sup>-1, B.E.R.=10<sup>-10</sup>, VR=Optimum with fc=1866MHz Bessel.



# InGaAs-APD/Preamp\_\_\_\_\_FRM5W232BS/BS-A Receiver Notes



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